ABSTRACT

SUBSTRATE PROCESSING METHOD AND
SUBSTRATE PROCESSING DEVICE

A processing tank 10 is divided into a washing section 15 and a drying section 30, a clearance is formed in the joint between the sections, and the clearance is communicated with by sink 29. In drying a substrate, the substrate is moved from the washing section to the drying section, a porous plate 28 is inserted into the lower region where the clearance is formed, and a drying gas is jetted against the substrate with the internal pressure of the drying section 30 kept higher than that of the sink 29 and the internal pressure of the washing section 15 kept lower than that of the drying section 30. In this case, it is preferable that the porous plate 28 is a punched plate in which plural small holes having predetermined diameters have been made. The above configuration provides a substrate processing method and a substrate processing device in which the drying gas can uniformly and stably be supplied to an assembly of plural substrates.

Fig. 1